

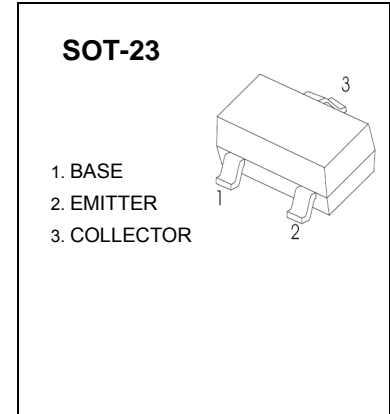


**SOT-23 Plastic-Encapsulate Transistors**

**2SC5344** TRANSISTOR (NPN)

**FEATURES**

- Audio power amplifier application
- High  $h_{FE}$  :  $h_{FE}=100\sim320$
- Complementary to 2SA1981



**MAXIMUM RATINGS (Ta=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CBO</sub>	Collector-Base Voltage	35	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	800	mA
P <sub>C</sub>	Collector Power Dissipation	200	mW
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 0.1mA, I <sub>B</sub> =0	35			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 10mA, I <sub>B</sub> =0	30			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 0.01mA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =35V, I <sub>E</sub> =0			0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = 5V, I <sub>C</sub> =0			0.1	μA
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =1V, I <sub>C</sub> = 100mA	100		320	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 500mA, I <sub>B</sub> =50mA			0.5	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA		120		MHz
Collector Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> = 0, f=1MHz		13		pF

**CLASSIFICATION OF h<sub>FE(1)</sub>**

Rank	O	Y
Range	100-200	160-320
Marking	FAO	FAY